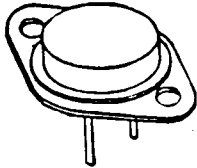


X00134

<b>SFT815</b> HIGH ENERGY FAST SWITCHING NPN POWER TRANSISTOR <b>90 AMPS, 300 VOLT</b>	<b>SSDI</b> 14849 FIRESTONE BLVD. LA MIRADA, CA. 90638 TEL (213) 921-9660 FAX (213) 921-2396
---	--

**CASE STYLE**  
JEDEC TO-3 WITH .060 PINS



**FEATURES**

- ▶ HIGH ENERGY
- ▶ FAST SWITCHING - tr 300 nsec MAX
- ▶ SINGLE CHIP CONSTRUCTION
- ▶ VERY LOW SATURATION
- ▶ HIGH GAIN TO 90 AMPS
- ▶ SUPERIOR PERFORMANCE TO  
SDT96301-SDT96303
- ▶ EUTECTIC DIE ATTACH
- ▶ HI-REL CONSTRUCTION

**MAXIMUM RATINGS**

RATING	SYMBOL	VALUE	UNIT
Collector-Emitter Voltage	VCEO	140	Volts
Collector-Base Voltage	VCBO	300	Volts
Emitter-Base Voltage	VEBO	10	Volts
Collector Current	IC	90	Amps
Base Current	IB	15	Amps
Total Device Dissipation @ Tc = 50 °C Derate Above 50 °C	PD	300 2	Watts W/ °C
Operating and Storage Temperature	TJ, Tstg	-65 to +200	°C

**THERMAL CHARACTERISTICS**

CHARACTERISTIC	SYMBOL	VALUE	UNIT
Thermal Resistance, Junction to Case	RθJC	0.5	°C/W

**ELECTRICAL CHARACTERISTICS**

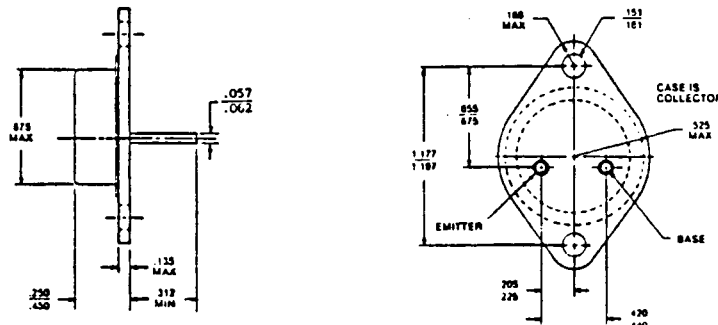
Characteristics	Symbol	Min	Max	Unit
Collector-Emitter Breakdown Voltage* (IC = 200mAdc)	BVCEO	140		Volts
Collector-Base Breakdown Voltage (IC = 100uAdc)	BVCBO	300		Volts

# ELECTRICAL CHARACTERISTICS

Characteristics		Symbol	Min	Max	Unit
Emitter-Base Breakdown Voltage ( $I_E = 100 \mu\text{A}$ )		BVEBO	10	-	Vdc
Collector Cutoff Current ( $V_{CB} = 200\text{Vdc}$ )		ICBO	-	10	$\mu\text{A}$
Emitter Cutoff Current ( $V_{EB} = 8\text{Vdc}$ )		IEBO	-	10	$\mu\text{A}$
DC Current Gain* ( $I_C = 30\text{A}$ , $V_{CE} = 5\text{Vdc}$ ) ( $I_C = 50\text{A}$ , $V_{CE} = 5\text{Vdc}$ ) ( $I_C = 90\text{A}$ , $V_{CE} = 5\text{Vdc}$ )		hFE	35 25 15	- - -	
Collector-Emitter Saturation Voltage* ( $I_C = 30\text{A}$ , $I_B = 3\text{A}$ ) ( $I_C = 50\text{A}$ , $I_B = 5\text{A}$ ) ( $I_C = 90\text{A}$ , $I_B = 9\text{A}$ )		VCE(SAT)	- - -	1.0 1.2 1.8	Vdc
Base-Emitter Saturation Voltage* ( $I_C = 30\text{A}$ , $I_B = 3\text{A}$ ) ( $I_C = 50\text{A}$ , $I_B = 5\text{A}$ ) ( $I_C = 90\text{A}$ , $I_B = 9\text{A}$ )		VBE(SAT)	- - -	1.2 1.6 2.0	Vdc
Current Gain Bandwidth Product ( $I_C = 1\text{A}$ , $V_{CE} = 10\text{Vdc}$ , $f = 1\text{MHz}$ )		fT	10	-	MHz
Output Capacitance ( $V_{CB} = 10\text{Vdc}$ , $I_E = 0\text{A}$ , $f = 1\text{MHz}$ )		Cob	-	800	pf
Second Breakdown Collector Current ( $t = 1\text{sec}$ , non repetitive, $V_{CE} = 30\text{V}$ )		IS/B	2		A
Delay Time	VCC = 100V, IC = 50A IB1 = IB2 = 1A VBB = -5V	td	-	0.1	$\mu\text{s}$
Rise Time		tr	-	0.3	$\mu\text{s}$
Storage Time		ts	-	1.8	$\mu\text{s}$
Fall Time		tf	-	0.3	$\mu\text{s}$

\*Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle = 2%

## PHYSICAL DIMENSIONS



SSDI

SOLID STATE DEVICES, INC.

14849 FIRESTONE BOULEVARD, LA MIRADA, CA 90638  
Telephone (213) 921-9660 ♦ FAX (213) 921-2396